

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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Application Number 09/726,903

Applicant

Lee Pooi See, et al.

Filing Date 11/29/00

Group Art Unit ~~none yet~~ 2823

U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	U.S. Patent Document No.	Name	Publication Date	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO

OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
JAC	1.	NYGREN, S., et al., "Morphological instabilities of nickel and cobalt silicides on silicon," Applied Surface Sciences (1991), pp. 87-91, vol. 53.
JAC	2.	SUN, et al., "Impact of Nitrogen (N ⁺ ₂) Implantation into Polysilicon Gate on Thermal Stability of Cobalt Silicide Formed on Polysilicon Gate," IEEE Transactions on Electron Devices (1998), pp. 1912-1919, vol. 45, no. 9.
JAC	3.	CHENG, L.W., et al., "Effects of nitrogen ion implantation on the formation of nickel silicide contacts on shallow junctions," Thin Solid Films 355-356. (1999), pp. 412-416.
JAC	4.	OHGURO, T., et al., "Nitrogen-doped nickel monosilicide technique for deep submicron CMOS salicide," IEEE IEDM Proc., (1995), pp. 453-456.
JAC	5.	DAS, S.R., et al., "Thermal Stability of Nickel Silicide Films," Mat. Res. Soc. Symp. Proc. (1996), pp. 541-545, vol. 427.

EXAMINER: (examiner)

DATE CONSIDERED:

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.